

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION					
Thermal Resistance (°C/W)					
Junction to	Ambient Mosfet	Ambient Schottky	Foot	Case Mosfet	Case Schottky
RT1	29.1251	26.9641	N/A	13.4788 u	96.6719 m
RT2	6.9670	7.9653	N/A	7.8166	9.2662
RT3	18.5814	21.9661	N/A	3.8770	2.5413
RT4	50.1265	52.8725	N/A	3.3831	3.9421
Thermal Capacitance (Joules/°C)					
Junction to	Ambient Mosfet	Ambient Schottky	Foot	Case Mosfet	Case Schottky
CT1	4.5843 m	1.5128 m	N/A	3.3132 u	552.5485 n
CT2	286.6328 u	183.5344 u	N/A	2.6699 m	2.7325 m
CT3	107.8828 m	26.6331 m	N/A	164.1397 u	489.1996 u
CT4	1.5756	1.3248	N/A	3.3130 m	40.4786 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION

R-C VALUES FOR FILTER CONFIGURATION					
Thermal Resistance ($^{\circ}\text{C}/\text{W}$)					
Junction to	Ambient Mosfet	Ambient Schottky	Foot	Case Mosfet	Case Schottky
RF1	9.1736	13.6647	N/A	5.5864	4.3064
RF2	28.8808	26.4897	N/A	2.3591	9.1143
RF3	18.7405	18.1736	N/A	6.5605	1.9761
RF4	47.9965	51.4571	N/A	511.4712 m	609.0441 m
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)					
Junction to	Ambient Mosfet	Ambient Schottky	Foot	Case Mosfet	Case Schottky
CF1	358.7743 u	236.2560 u	N/A	174.6616 u	461.3789 u
CF2	4.3863 m	1.7918 m	N/A	1.8003 m	2.7165 m
CF3	89.7908 m	37.0519 m	N/A	183.9506 u	51.2715 m
CF4	1.5299	1.3457	N/A	5.4784 m	1.3402

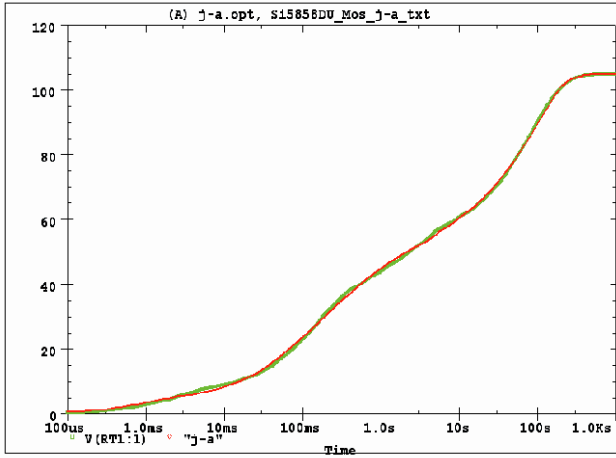
Note: NA indicates not applicable

Reference:

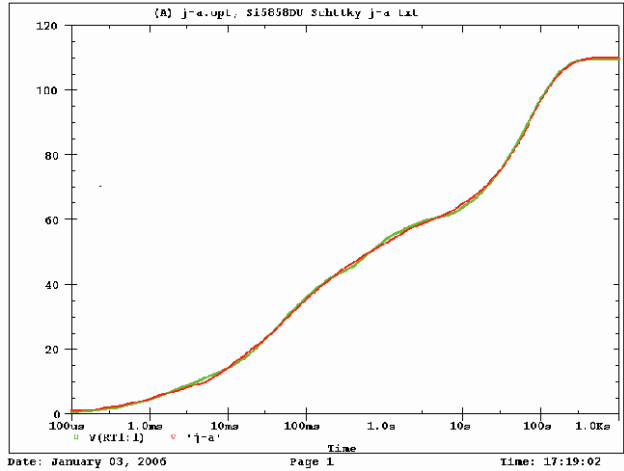
[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002



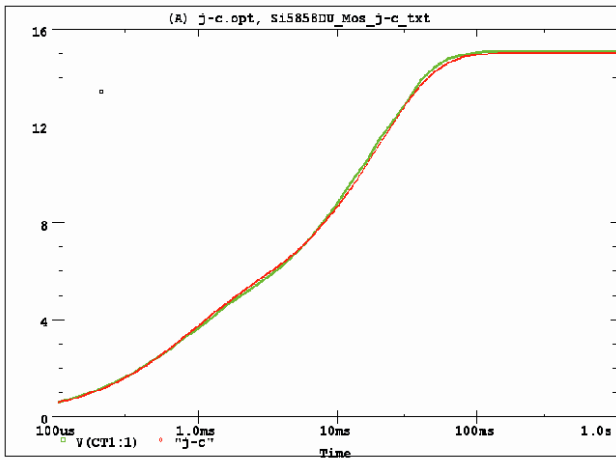
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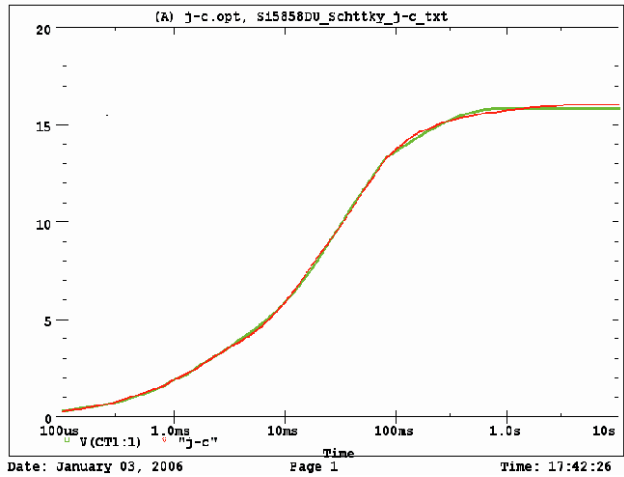
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Si5858DU Mosfet Tank j-c Temperature: 27.0

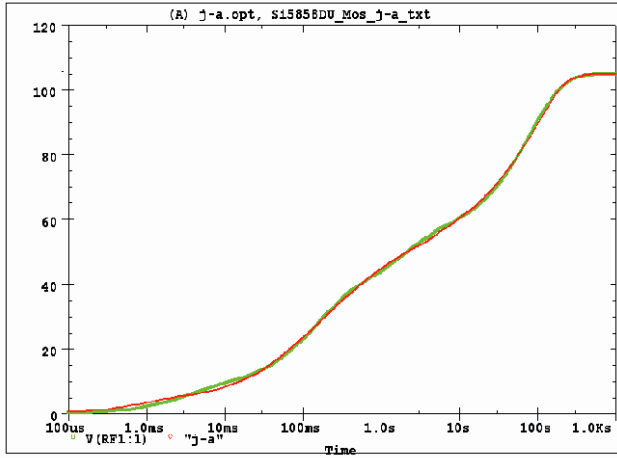


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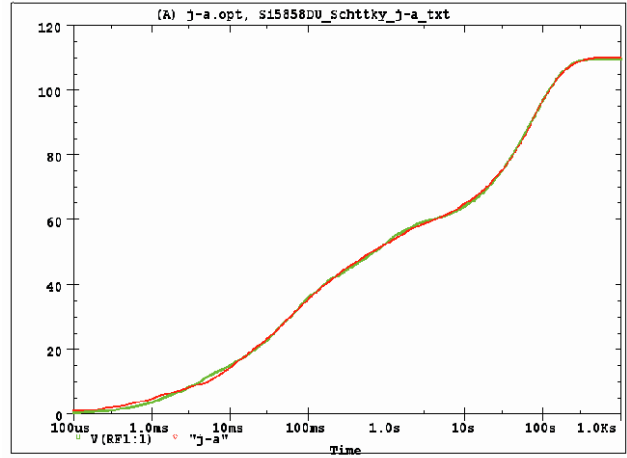


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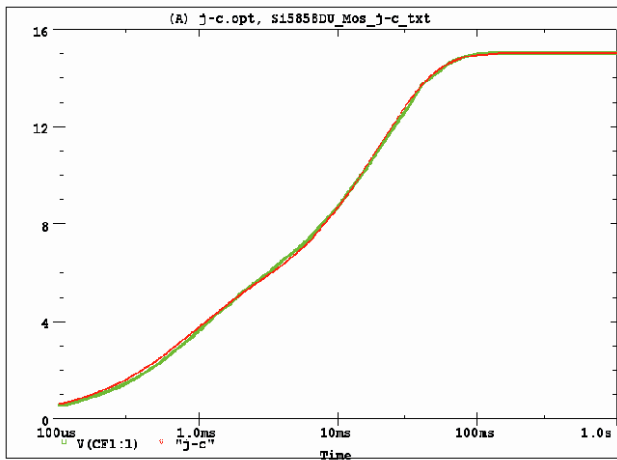
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Si5858DU Schottky Filter j-a Temperature: 27.0



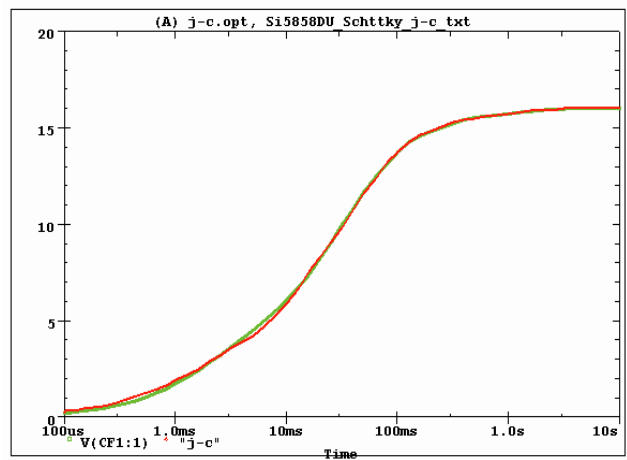
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